

## REMARKS

This Amendment is in response to the Office Action dated March 17, 2003.

Claims 1-21 are pending in the present application. Claims 10-21 have been rejected.

Claims 1-9 have been withdrawn from consideration. Accordingly, claims 10-21 are pending in the present application. For the reasons set forth more fully below, Applicant respectfully submits that the claims as presented are allowable. Consequently, reconsideration, allowance, and passage to issue are respectfully requested.

### Specification

The Examiner has stated:

2. There is no description of figure 2g. What are 31 and 33 in figure 2g?

Applicant has amended the specification to describe Figure 2g.

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### Claim Rejections – 35 U.S.C. 103

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The Examiner has stated,

4. Claims 10-21 are rejected under U.S.C. 103(a) as being unpatentable over Yamada (6,008,127) in view of Dausch et al (6,359,374 B1).

Regarding claim 10, 16, Yamada, figures 1-38 (figures 33, 35, 36, 37, col. 8, lines 52-67, col. 9, lines 1-67), disclose a semiconductor device comprising: a semiconductor substrate 201 including a plurality of device structures (see figure 35) thereon; and an interconnect 235 on the semiconductor substrate, the interconnect comprising at least one slot 235 (see figure 33) provided in the semiconductor substrate and at least one metal 235 (aluminum) within the slot, wherein the at least one slot is oxidized everywhere (see col. 8, lines 52-67) except at the bottom of the slot where the interconnect forms a ground 225 (see col. 9, lines 58-65). Yamada fails to teach the at least one metal being of sufficient thickness to carry a high current.

However, Dausch, figures 1-4, and related text on col. 1-10, (col. 5, lines 14-24, col. 6, lines 24-58) teach at least one metal being of sufficient thickness to carry

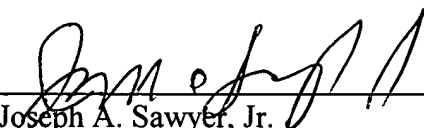
a high current. Regarding to claims 11-15, 17-21, see Yamada, col. 1-14, and Dausch, col. 1-10. It would have been obvious to one having ordinary skill in the art at the time of the present invention to apply the teachings of Dausch into the method of Yamada as both are related to the same subject matter of providing a high voltage semiconductor device including an interconnection layer having at least one metal within a slot. The conductive metal with sufficient thickness to carry a high current.

Applicant respectfully disagrees. Firstly, the arguments made previously with respect to Yamada in the amendment dated January 29, 2003 are incorporated by reference herein. Applicant agrees with Examiner that Yamada fails to teach "the at least one metal being of sufficient thickness to carry a high current." Dausch however does not provide this feature. Dausch is directed to miniature electric relays. This disclosure is clearly non-analogous art. To combine these references in this manner can only be done by reviewing the present application. Therefore, applicant submits that is impermissible hindsight reasoning. Applicant submits therefore that the claims are allowable over the cited references.

Accordingly, Applicant's attorney believes that this application is in condition for allowance. Should any unresolved issues remain, Examiner is invited to call Applicant's attorney at the telephone number indicated below.

Respectfully submitted,  
SAWYER LAW GROUP LLP

November 19, 2003  
Date

  
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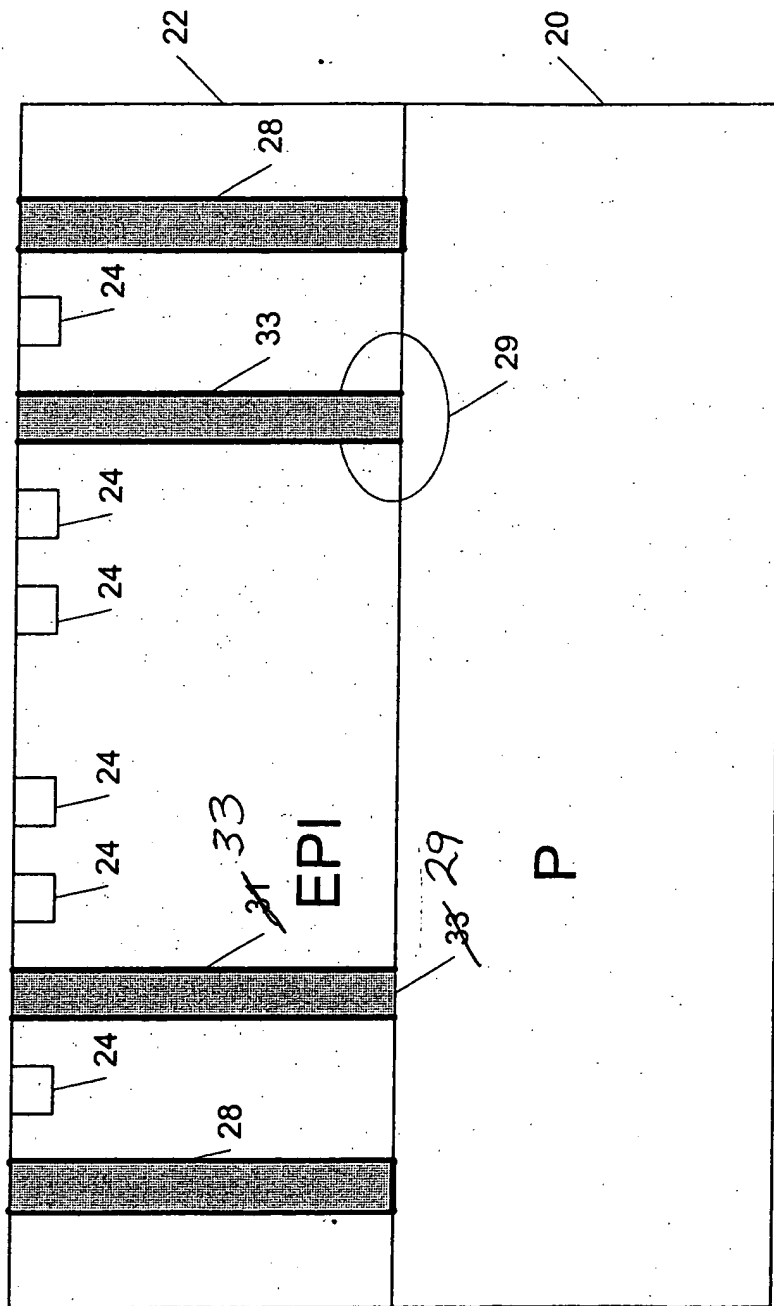


Fig. 2g